
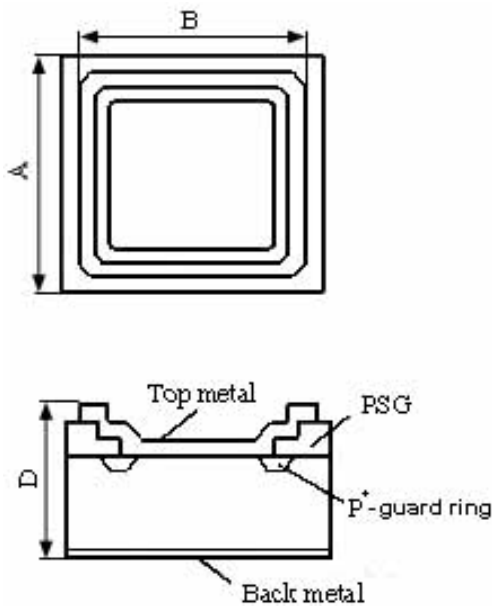


# SCHOTTKY DIODES KDN-05060.



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>	<b>5A/60V. Die Size-65mil.</b>			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	5,0	-
DC Forward Voltage @ 25°C, $I_F=5,0A$	$V_F$	V	0,65	0,63
Maximum Reverse Current  @ 25°C, $V_R=65V$ 25°C, $V_R=60V$ 125°C, $V_R=60V$	$I_R$	mA	- 0,100 50,0	0,100 0,080 45,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	110	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150^\circ C$ .	$I_{RRM}$	A	2,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	150	



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	1650 1650
$B_x$ $B_y$	Top Metal Size	1510 1510
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.

*Backside metal:* **Ti-Ni-Ag**.